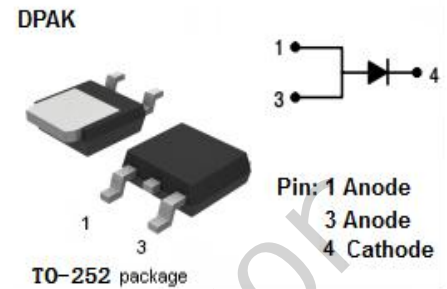


FEATURES

- Schottky barrier chip
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Operating Junction Temperature
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


APPLICATIONS

- For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, DC-to-DC converters or polarity protection application.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RMS} V _R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	35	V
I _{F(AV)}	Average Rectified Forward Current	8	A
I _{FSM}	Non-repetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	175	A
T _J	Junction Temperature	-65~125	°C
T _{stg}	Storage Temperature Range	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.8	°C/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
V _F	Maximum Instantaneous Forward Voltage	I _F = 8A ; T _J = 25°C		0.51	V
		I _F = 8A ; T _J = 125°C		0.41	
I _R	Maximum Instantaneous Reverse Current	V _R = V _{RRM} ; T _J = 25°C		1.4	mA
		V _R = V _{RRM} ; T _J = 100°C		35	

Package Dimensions

